

SANYO

No.1880B

DTM12-N

Silicon Planar Type

12A Bidirectional Thyristor**Features**

- Insulation type
- Peak OFF-state voltage : 200 to 600V
- RMS ON-state current : 12A
- TO-220 package

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

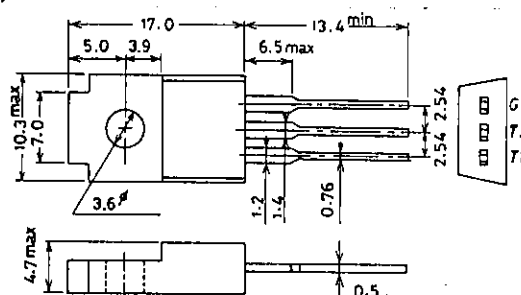
			DTM 12C-N	DTM 12E-N	DTM 12G-N	unit
Repetitive Peak OFF-State Voltage	V_{DRM}		200	400	600	V
RMS ON-State Current	$I_{\text{T(RMS)}}$	$T_c = 73^\circ\text{C}$, single-phase full-wave	→	→	12	A
Surge ON-State Current	I_{TSM}	Peak 1 cycle, 50Hz	→	→	100	A
Amperes Squared-Seconds	$i^2t \cdot dt$	$1\text{ms} \leq t \leq 10\text{ms}$	→	→	50	A^2S
Peak Gate Power Dissipation	P_{GM}	$f \geq 50\text{Hz}$, duty $\leq 10\%$	→	→	5	W
Average Gate Power Dissipation	$P_{\text{G(AV)}}$		→	→	0.5	W
Peak Gate Current	I_{GM}	$f \geq 50\text{Hz}$, duty $\leq 10\%$	→	→	± 2	A
Peak Gate Voltage	V_{GM}	$f \geq 50\text{Hz}$, duty $\leq 10\%$	→	→	± 10	V
Junction Temperature	T_j		→	→	125	$^\circ\text{C}$
Storage Temperature	T_{stg}		→	→	-40 to +125	$^\circ\text{C}$
Weight			→	→	2.1	g

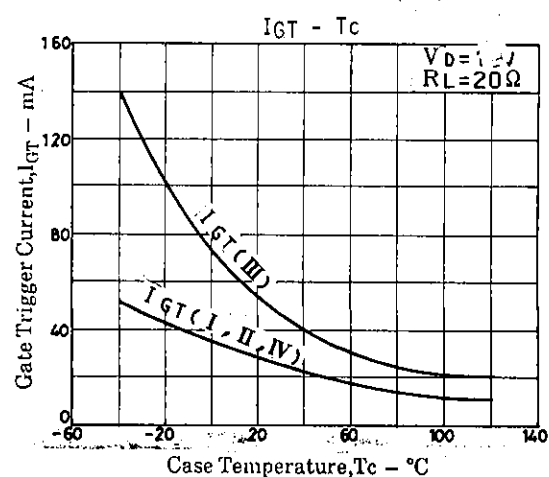
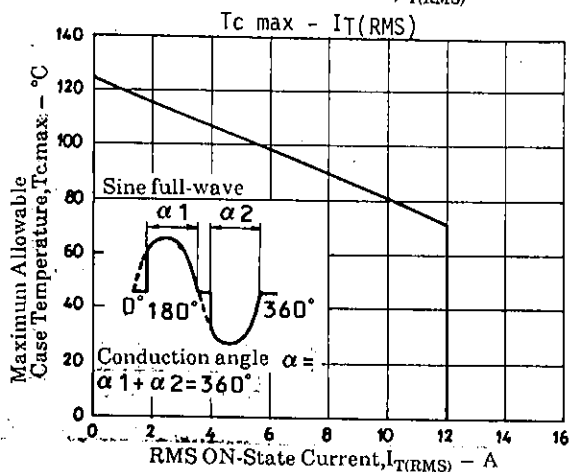
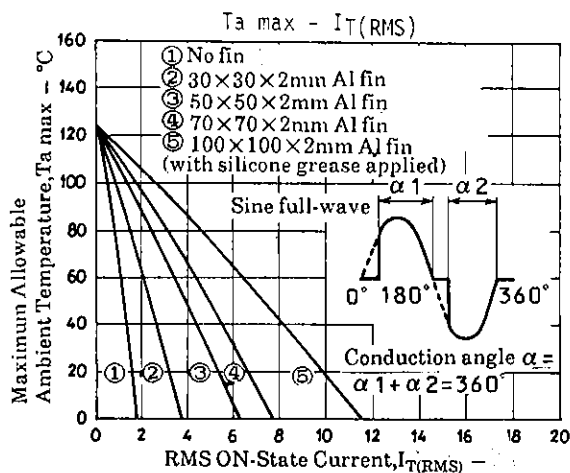
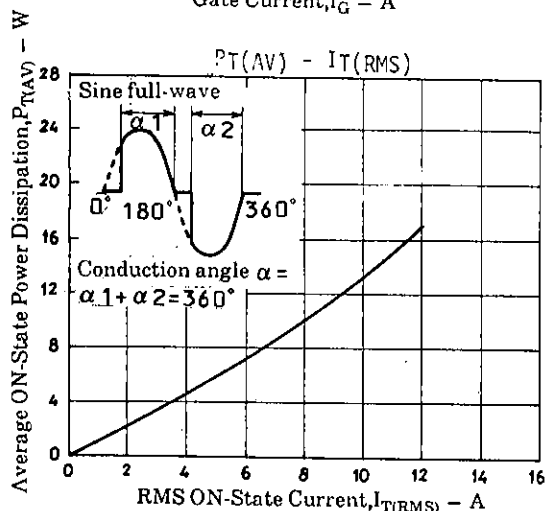
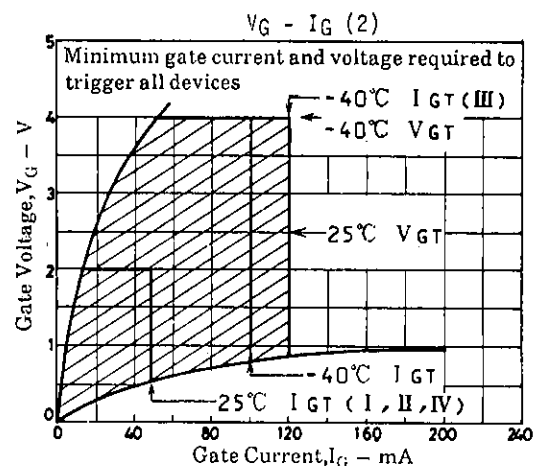
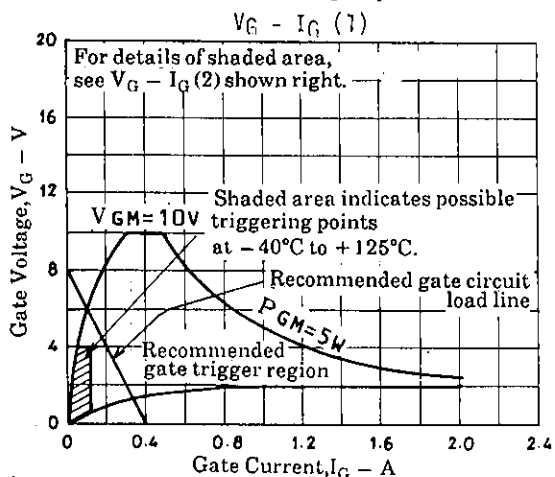
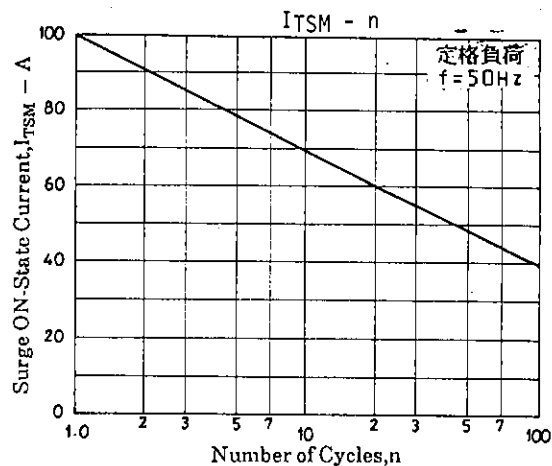
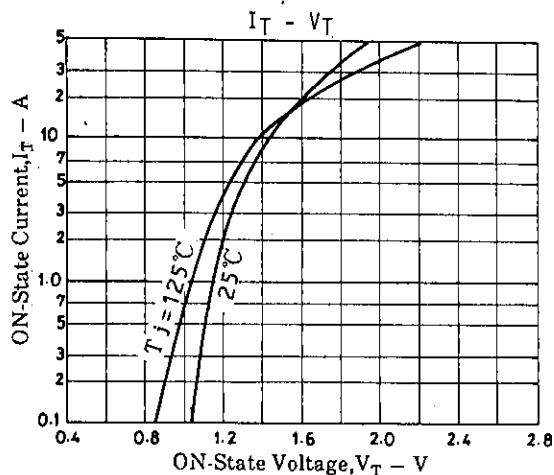
Electrical Characteristics at $T_a = 25^\circ\text{C}$

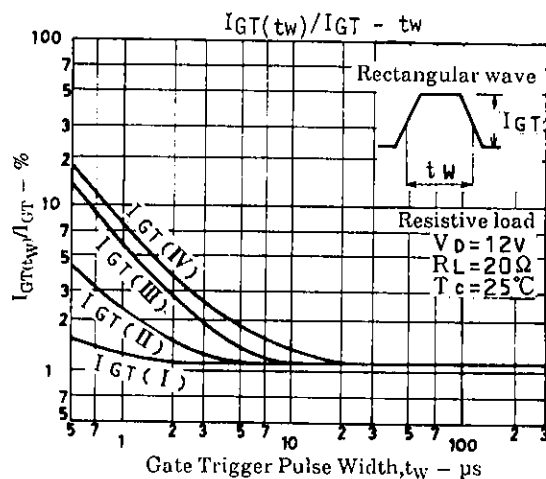
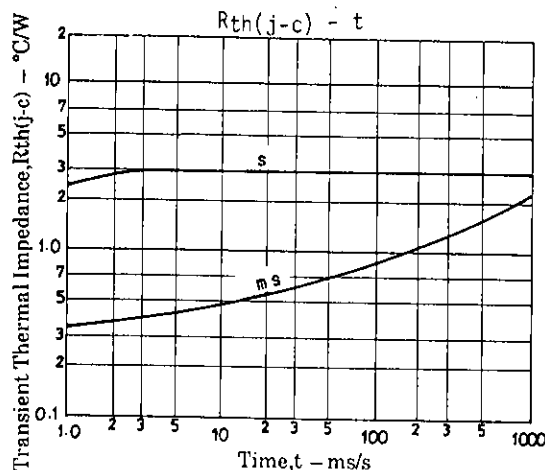
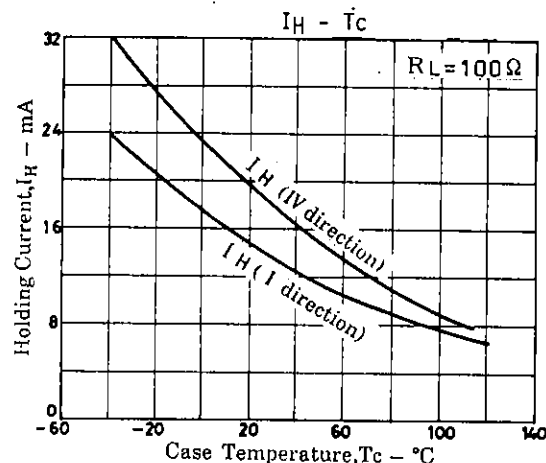
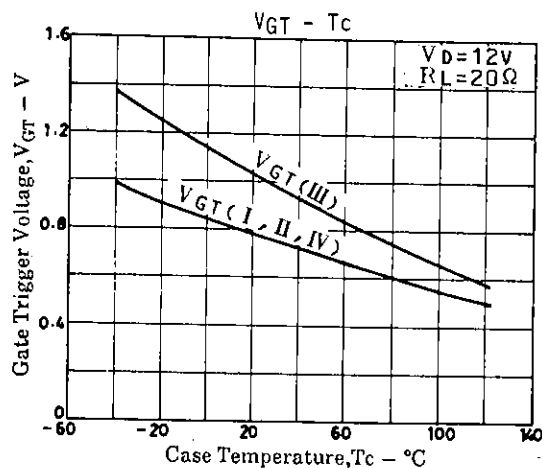
			min	typ	max	unit
Repetitive Peak OFF-State Current	I_{DRM}	$T_j = 125^\circ\text{C}$, $V_D = V_{\text{DRM}}$			2	mA
Peak ON-State Voltage	V_{TM}	$I_{\text{TM}} = 12\text{A}$			1.5	V
Critical Rate of Rise of OFF-State Voltage	$(dv/dt)_c$	$T_j = 125^\circ\text{C}$, $V_D = 200\text{V(C)}$, 400V(E to G)	10			V/ μs
Holding Current	I_{H}	$R_L = 100\Omega$			50	mA
Gate Trigger Current※ (I)	I_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			30	mA
(II)	I_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			30	mA
(III)	I_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			50	mA
(IV)	I_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			30	mA
Gate Trigger Voltage※ (I)	V_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			2	V
(II)	V_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			2	V
(III)	V_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			2	V
(IV)	V_{GT}	$V_D = 12\text{V}$, $R_L = 20\Omega$			2	V
Gate Nontrigger Voltage	V_{GD}	$T_c = 125^\circ\text{C}$, $V_D = V_{\text{DRM}}$	0.2			V
Thermal Resistance	$R_{\text{th(j-c)}}$	Between junction and case, AC			3.0	$^\circ\text{C/W}$

※ : The gate trigger mode is shown below. **Package Dimensions 1144**
(unit: mm)

Trigger mode	T2	T1	G
I	+	-	+
II	+	-	-
III	-	+	+
IV	-	+	-







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